

KSC4468

Audio Power Amplifier

- High Current Capability : I_C=15A
- High Power Dissipation
- Wide S.O.A
- Complement to KSA1695



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	140	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current (DC)	8	Α
I _{CP}	Collector Current (Pulse)	16	А
PC	Collector Dissipation (T _C =25°C)	80	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =5mA, I _E =0	160			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, R _{BE} =∞	140			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =5mA, I _C =0	6			V
I _{CBO}	Collector Cut-off Current	V _{CB} =80V, I _E =0			0.1	mA
I _{EBO}	Emitter Cut-off Current	V_{EB} =4V, I_{C} =0			0.1	mA
h _{FE1}	* DC Current Gain	V _{CE} =5V, I _C =1A	60		200	
h_{FE2}		V _{CE} =5V, I _C =6A	20			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =5A, I _B =0.5A			2.5	V
V _{BE} (on)	Base-Emitter ON Voltage	V _{CE} =5V, I _C =1A			1.5	V
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =1A		30		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, f=1MHz		210		pF
t _{ON}	Turn ON Time	V _{CC} =20V,		0.26		μs
t _F	Fall Time	$I_{C}=1A=10I_{B1}=-10I_{B2}$		0.68		μs
t _{STG}	Storage Time	$R_L=20\Omega$		6.68		μs

* Pulse Test : PW=20μs

$h_{\mbox{\scriptsize FE}}$ Classification

Classification	0	Y	
h _{FE1}	60 ~ 120	100 ~ 200	

Typical Characteristics

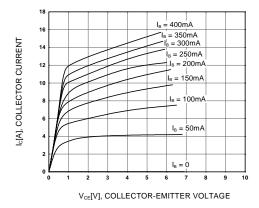


Figure 1. Static Characterstic

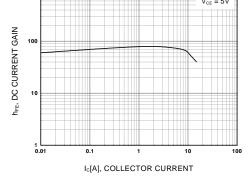


Figure 2. DC current Gain

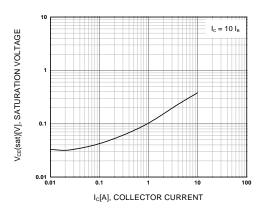


Figure 3. Collector-Emitter Saturation Voltage

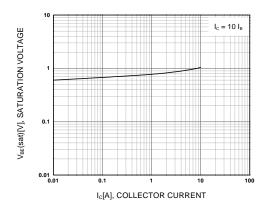


Figure 4. Base-Emitter Saturation Voltage

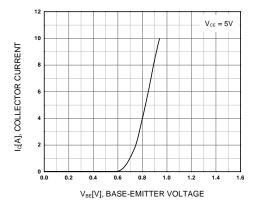
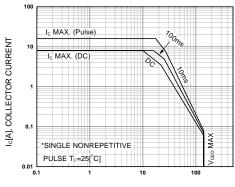


Figure 5. Base-Emitter On Voltage



 $V_{\text{CE}}[V]$, COLLECTOR-EMITTER VOLTAGE

Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

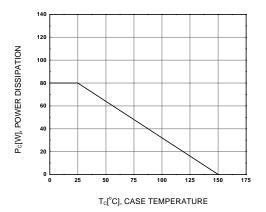
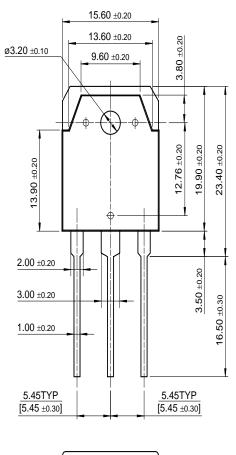


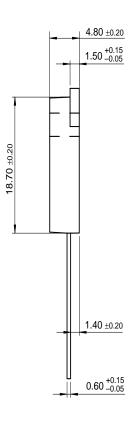
Figure 7. Power Derating

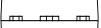
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Package Demensions

TO-3P







Dimensions in Millimeters

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